

1) Find the resistance of an intrinsic Ge rod of 1cm long, 1mm wide and 1mm thick at 300k. The intrinsic carrier density is $2.5 \times 10^{19} \text{ m}^{-3}$ at 300k and the mobility of e^- and hole are 0.39 and $0.19 \text{ m}^2 \text{ v}^{-1} \text{ s}^{-1}$.

S/ $l = 1 \text{ cm} = 1 \times 10^{-2} \text{ m}$, $b = 1 \text{ mm} = 1 \times 10^{-3} \text{ m}$, $t = 1 \text{ mm} = 1 \times 10^{-3} \text{ m}$

$T = 300 \text{ K}$, $n_i = 2.5 \times 10^{19} \text{ m}^{-3}$, $\mu_e = 0.39 \text{ m}^2 \text{ v}^{-1} \text{ s}^{-1}$

$\mu_h = 0.19 \text{ m}^2 \text{ v}^{-1} \text{ s}^{-1}$

Conductivity (σ) = $n_i e (\mu_e + \mu_h)$
 $= 2.5 \times 10^{19} \times 1.6 \times 10^{-19} \times (0.39 + 0.19)$
 $= 2.32 \text{ } \Omega^{-1} \text{ m}^{-1}$

Resistivity (ρ_i) = $\frac{1}{\sigma_i} = \frac{1}{2.32} = 0.431 \text{ } \Omega \text{ m}$

Resistance (R) = $\frac{\rho l}{A} = \frac{0.431 \times 1 \times 10^{-2}}{1 \times 10^{-3} \times 1 \times 10^{-3}} = 4310 \text{ } \Omega$

2) The intrinsic carrier density $1.5 \times 10^{16} \text{ m}^{-3}$ of the mobility of e^- and hole are 0.13 and $0.05 \text{ m}^2 \text{ v}^{-1} \text{ s}^{-1}$ respectively. Calculate the Conductivity.

S/ $n_i = 1.5 \times 10^{16} \text{ m}^{-3}$, $\mu_e = 0.13 \text{ m}^2 \text{ v}^{-1} \text{ s}^{-1}$, $\mu_h = 0.05 \text{ m}^2 \text{ v}^{-1} \text{ s}^{-1}$

$\sigma = n_i e (\mu_e + \mu_h)$
 $= 1.5 \times 10^{16} \times 1.6 \times 10^{-19} \times (0.13 + 0.05)$
 $= 4.32 \times 10^{-3} \text{ } \Omega^{-1} \text{ m}^{-1}$

3) For an intrinsic semiconductor with a bandgap of 0.7eV. Determine the position of F_f at $T = 300 \text{ K}$ if $m_h^* = 6m_e^*$

S/ $E_g = 0.7 \text{ eV} = 0.7 \times 1.6 \times 10^{-19} = 1.12 \times 10^{-19} \text{ J}$

$T = 300 \text{ K}$

$E_f = \frac{E_g}{2} + \frac{3kT}{4} \log \left[\frac{m_h^*}{m_e^*} \right]$
 $= \frac{1.12 \times 10^{-19}}{2} + \frac{3 \times 1.38 \times 10^{-23} \times 300}{4} \log [6]$

$= 5.6 \times 10^{-20} + 5.5634 \times 10^{-21}$

$E_f = 6.15634 \text{ J (or)} = \frac{6.15634}{1.6 \times 10^{-19}} \text{ eV} = 0.3847 \text{ eV}$

5) Calculate the cut off wavelength for Si Photodiode if its bandgap is 1.1ev.

$$\lambda_c = \frac{hc}{E_g} = \frac{6.626 \times 10^{-34} \times 3 \times 10^8}{1.1 \times 1.6 \times 10^{-19}} = 1.129 \mu\text{m.}$$

6) The conductivity of Ge at 20°C is $2 \Omega^{-1} \text{m}^{-1}$. What is its conductivity at 40°C. $E_g = 0.72 \text{ eV}$.

$$\sigma = \sigma_0 e^{-E_g/2k_B T}$$

$$\sigma_1 = \sigma_0 e^{-E_g/2k_B T_1}$$

$$\sigma_2 = \sigma_0 e^{-E_g/2k_B T_2}$$

$$\sigma_2 = \sigma_1 \cdot \frac{e^{-E_g/2k_B T_1}}{e^{-E_g/2k_B T_2}}$$

$$= 2 e^{\frac{(-0.72 \times 1.6 \times 10^{-19})}{(2 \times 1.38 \times 10^{-23} \times 313)}}$$

$$e^{\frac{(-0.72 \times 1.6 \times 10^{-19})}{(2 \times 1.38 \times 10^{-23} \times 293)}}$$

$$\sigma_2 = 1.0002 \Omega^{-1} / \text{m}$$

